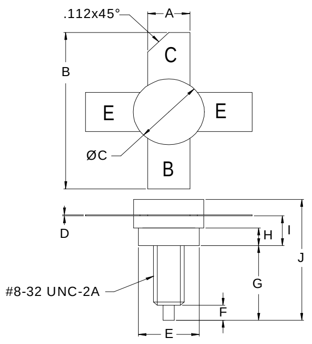
NPN SILICON RF POWER TRANSISTOR

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

DESCRIPTION:

The **MRF238** is Designed for 13.6 V FM Large-Signal Amplifier Applications to 175 MHz.

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CE}	18 V
V_{CB}	60 V
P_{DISS}	65 W @ T_C = 25 °C
T_{STG}	-65 °C to +150 °C

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 15 mA	36			**V**
BV_{CEO}	I_C = 100 mA	18			**V**
BV_{EBO}	I_E = 5.0 mA	4.0			**V**
I_{CBO}	V_{CB} = 30 V			2.0	**mA**
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	5.0			**---**
C_{ob}	V_{CB} = 15 V f = 1.0 MHz		105	130	**pF**
G_{PE}	V_{CC} = 13.6 V P_{out} = 30 W f = 160 MHz	9.0	10		**dB**
η		60			**%**